



Edition 1.0 2019-04

# INTERNATIONAL STANDARD



Semiconductor devices – Micro-electromechanical devices – Part 31: Four-point bending test method for interfacial adhesion energy of layered MEMS materials

> <u>IEC 62047-31:2019</u> https://standards.iteh.ai/catalog/standards/sist/a19045bf-d653-48a1-89afa4bd23f31c73/iec-62047-31-2019





# THIS PUBLICATION IS COPYRIGHT PROTECTED Copyright © 2019 IEC, Geneva, Switzerland

All rights reserved. Unless otherwise specified, no part of this publication may be reproduced or utilized in any form or by any means, electronic or mechanical, including photocopying and microfilm, without permission in writing from either IEC or IEC's member National Committee in the country of the requester. If you have any questions about IEC copyright or have an enquiry about obtaining additional rights to this publication, please contact the address below or your local IEC member National Committee for further information.

IEC Central Office 3, rue de Varembé CH-1211 Geneva 20 Switzerland Tel.: +41 22 919 02 11 info@iec.ch www.jec.ch

### About the IEC

The International Electrotechnical Commission (IEC) is the leading global organization that prepares and publishes International Standards for all electrical, electronic and related technologies.

### About IEC publications

The technical content of IEC publications is kept under constant review by the IEC. Please make sure that you have the latest edition, a corrigendum or an amendment might have been published.

### IEC publications search - webstore.iec.ch/advsearchform

The advanced search enables to find IEC publications by a variety of criteria (reference number, text, technical committee,...). It also gives information on projects, replaced and withdrawn publications.

### IEC Just Published - webstore.iec.ch/justpublished Stay up to date on all new IEC publications. Just Published

Stay up to date on all new IEC publications. Just Published details all new publications released. Available online and once a month by email.

IEC Customer Service Centre - webstore lie ch/csc and collected If you wish to give us your feedback on this publication or need further assistance, please contact the Customer Service Centre: sales@iec.ch. IEC 62047-31:2019

### Electropedia - www.electropedia.org

The world's leading online dictionary on electrotechnology, containing more than 22 000 terminological entries in English and French, with equivalent terms in 16 additional languages. Also known as the International Electrotechnical Vocabulary (IEV) online.

### IEC Glossary - std.iec.ch/glossary

67 000 electrotechnical terminology entries in English and French extracted from the Terms and Definitions clause of IEC publications issued since 2002. Some entries have been collected from earlier publications of IEC TC 37, 77, 86 and CISPR.

https://standards.iteh.ai/catalog/standards/sist/a19045bf-d653-48a1-89afa4bd23f31c73/iec-62047-31-2019



Edition 1.0 2019-04

# INTERNATIONAL STANDARD



# Semiconductor devices – Micro-electromechanical devices – Part 31: Four-point bending test method for interfacial adhesion energy of layered MEMS materials

<u>IEC 62047-31:2019</u> https://standards.iteh.ai/catalog/standards/sist/a19045bf-d653-48a1-89afa4bd23f31c73/iec-62047-31-2019

INTERNATIONAL ELECTROTECHNICAL COMMISSION

ICS 31.080.99

ISBN 978-2-8322-6717-2

Warning! Make sure that you obtained this publication from an authorized distributor.

# CONTENTS

FOREWORD	3
1 Scope	5
2 Normative references	5
3 Terms, definitions, symbols and designations	5
3.1 Terms and definitions	5
3.2 Symbols and designations	6
4 Test piece	6
4.1 General	6
4.2 Shape of a test piece	6
4.3 Measurement of dimensions	7
4.4 Evaluation of energy release rate	7
5 Testing method and test apparatus	7
5.1 Test principle	7
5.2 Test machine	8
5.3 Test procedure	8
5.4 Test environment	9
6 Test report	9
Annex A (informative) Failure modes during the four-point bending test	10
A.1 General	10
A.2 Some failure modes ( <b>Standards.iteh.ai</b> )	10
Bibliography	12
<u>IEC 62047-31:2019</u> https://standards.iteb.ai/catalog/standards/sist/a10045hf.d653_48a1_89af	
Figure 1 – Four-point bending test piece $3_{10}$ $7_{10$	6
Figure 2 – Picture of a four-point bending fixture	9
Figure A.1 – Several failure modes during the four-point bending test	
5	
Table 1 – Symbols and designations of a test piece	6

# INTERNATIONAL ELECTROTECHNICAL COMMISSION

# SEMICONDUCTOR DEVICES – MICRO-ELECTROMECHANICAL DEVICES –

# Part 31: Four-point bending test method for interfacial adhesion energy of layered MEMS materials

# FOREWORD

- 1) The International Electrotechnical Commission (IEC) is a worldwide organization for standardization comprising all national electrotechnical committees (IEC National Committees). The object of IEC is to promote international co-operation on all questions concerning standardization in the electrical and electronic fields. To this end and in addition to other activities, IEC publishes International Standards, Technical Specifications, Technical Reports, Publicly Available Specifications (PAS) and Guides (hereafter referred to as "IEC Publication(s)"). Their preparation is entrusted to technical committees; any IEC National Committee interested in the subject dealt with may participate in this preparatory work. International, governmental and non-governmental organizations liaising with the IEC also participate in this preparation. IEC collaborates closely with the International Organization for Standardization (ISO) in accordance with conditions determined by agreement between the two organizations.
- 2) The formal decisions or agreements of IEC on technical matters express, as nearly as possible, an international consensus of opinion on the relevant subjects since each technical committee has representation from all interested IEC National Committees. TANDARD PREVIEW
- interested IEC National Committees. TANDARD PREVIEW
  3) IEC Publications have the form of recommendations for international use and are accepted by IEC National Committees in that sense. While all reasonable efforts are made to ensure that the technical content of IEC Publications is accurate, IEC cannot be held responsible for the way in which they are used or for any misinterpretation by any end user.
- 4) In order to promote international uniformity <u>FIEC(National)Committees</u> undertake to apply IEC Publications transparently to the maximum extent possible in their national and regional publications. Any divergence between any IEC Publication and the corresponding national or regional publication shall be clearly indicated in the latter.
- 5) IEC itself does not provide any attestation of conformity. Independent certification bodies provide conformity assessment services and, in some areas, access to IEC marks of conformity. IEC is not responsible for any services carried out by independent certification bodies.
- 6) All users should ensure that they have the latest edition of this publication.
- 7) No liability shall attach to IEC or its directors, employees, servants or agents including individual experts and members of its technical committees and IEC National Committees for any personal injury, property damage or other damage of any nature whatsoever, whether direct or indirect, or for costs (including legal fees) and expenses arising out of the publication, use of, or reliance upon, this IEC Publication or any other IEC Publications.
- 8) Attention is drawn to the Normative references cited in this publication. Use of the referenced publications is indispensable for the correct application of this publication.
- 9) Attention is drawn to the possibility that some of the elements of this IEC Publication may be the subject of patent rights. IEC shall not be held responsible for identifying any or all such patent rights.

International Standard IEC 62047-31 has been prepared by subcommittee 47F: Microelectromechanical systems, of IEC technical committee 47: Semiconductor devices.

The text of this International Standard is based on the following documents:

FDIS	Report on voting
47F/326/FDIS	47F/331RVD

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 62047 series, published under the general title *Semiconductor devices* – *Micro-electromechanical devices*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under "http://webstore.iec.ch" in the data related to the specific document. At this date, the document will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

A bilingual version of this publication may be issued at a later date.

IMPORTANT – The 'colour inside' logo on the cover page of this publication indicates that it contains colours which are considered to be useful for the correct understanding of its contents. Users should therefore print this document using a colour printer.

# iTeh STANDARD PREVIEW (standards.iteh.ai)

<u>IEC 62047-31:2019</u> https://standards.iteh.ai/catalog/standards/sist/a19045bf-d653-48a1-89afa4bd23f31c73/iec-62047-31-2019

# SEMICONDUCTOR DEVICES – MICRO-ELECTROMECHANICAL DEVICES –

# Part 31: Four-point bending test method for interfacial adhesion energy of layered MEMS materials

## 1 Scope

This part of IEC 62047 specifies a four-point bending test method for measuring interfacial adhesion energy of the weakest interface in the layered micro-electromechanical systems (MEMS) based on the concept of fracture mechanics. In a variety of MEMS devices, there are many layered material interfaces, and their adhesion energies are critical to the reliability of the MEMS devices. The four-point bending test utilizes a pure bending moment applied to a test piece of layered MEMS device, and the interfacial adhesion energy is measured from the critical bending moment for the steady state cracking in the weakest interface. This test method applies to MEMS devices with thin film layers deposited on semiconductor substrates. The total thickness of the thin film layers should be 100 times less than the thickness of a supporting substrate (typically a silicon wafer piece).

# 2 Normative references STANDARD PREVIEW

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

ps://standards.iteh.ai/catalog/standards/sist/a19045bf-d653-48a1-89af-

There are no normative references in this document.

# 3 Terms, definitions, symbols and designations

### 3.1 Terms and definitions

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at http://www.electropedia.org/
- ISO Online browsing platform: available at http://www.iso.org/obp

# 3.1.1 energy release rate

strain energy per unit surface area, which is released during the incremental growth of a crack

Note 1 to entry: The energy release rate can be regarded as the crack driving force, and its unit is given in J/m<sup>2</sup>.

# 3.1.2 interfacial adhesion energy *G*<sub>C</sub>

critical energy release rate at the moment of crack extension

Note 1 to entry: Its unit is given in: J/m<sup>2</sup>.

### 3.2 Symbols and designations

The shape of the test piece and the symbols are presented in Figure 1 and Table 1, respectively. The overall shape of the test piece is similar to a sandwiched cantilever beam, and it should have a pre-crack or a notch for crack initiation. After initiation of the crack, the crack follows the weakest interface in the layered materials system.



### Key

- 1 layered material
- 2 notched pre-crack iTeh STANDARD PREVIEW
- 3 interfacial crack

# (standards.iteh.ai)

Figure 1 – Four-point bending test piece

IEC 62047-31:2019

## hTablea1derCymbolsabgdadesignations5of a test piece-

Symbol	Unit	Designation
L	mm	Spacing between two adjacent pins
b	mm	Width
h	μm	Thickness of the supporting structure
Р	Ν	Force for driving crack

# 4 Test piece

### 4.1 General

The test piece for the layered MEMS materials shall be prepared using the same fabrication process that applies to actual MEMS devices. Machining of the test piece shall be performed to prevent formation of unintended cracks or flaws and delamination in the test piece.

## 4.2 Shape of a test piece

The overall shape of a test piece is shown in Figure 1. Because the evaluation of the energy release rate relies on several simplifying assumptions, the geometric shape of the test piece should be designed as follows: the thickness of the test piece should be 50 times less than the length and width of the test piece, and the length should be 10 times larger than the width. The total thickness of the layered materials should be 100 times less than the thickness of a supporting substrate. A pre-crack or notch shown in Figure 1 is machined using conventional ways like a diamond saw, laser ablation, or chemical etching. This pre-crack initiates cracking in the supporting substrate under bending, and after that the cracking leads to the introduction

of an interface crack between two adjacent layers of the weakest interface in the layered materials.

#### 4.3 Measurement of dimensions

To analyze the test results, the test piece dimensions shall be accurately measured because the dimensions are used to determine the mechanical properties of test materials. Spacing between the pins (L), width (b), and thickness (h) should be measured with an error of less than ±5 %. Information on thickness measurement can be found in IEC 62047-2:2006, Annex C and in IEC 62047-3:2006, Clause 6.

#### 4.4 Evaluation of energy release rate

The energy release rate (G) is evaluated using the following Equation (1):

$$G = \frac{21(1-\nu^2)P^2L^2}{16Eb^2h^3}$$
(1)

where

- is Poisson's ratio; ν
- is Young's modulus; Ε
- is the width of a test piece TANDARD PREVIEW h
- is the thickness of the supporting structures.iteh.ai) h
- L is the spacing between two adjacent pins, and
- IEC 62047-31:2019 Р is the applied load.

https://standards.iteh.ai/catalog/standards/sist/a19045bf-d653-48a1-89af-The critical energy release rate aqid the interfacial 7ad besion energy is evaluated from the energy release rate when the interfacial crack lying in the interface starts to grow. This formula is valid for brittle fracture.

### Testing method and test apparatus 5

#### 5.1 **Test principle**

The test is performed by applying a pure bending moment to a test piece with a layered material interface as shown in Figure 1. The test consists of two steps: the first is the introduction of an interface crack between two layered materials with the weakest interface. By gradually increasing the four-point bending load applied to the test piece, a crack is initiated from a machined pre-crack. The initiated crack extends in a direction of thickness and then becomes an interface crack when it touches the weakest interface. When the interface crack is formed, the bending load is relaxed. The second step is the extension of the interface crack. By reloading the bending load, the energy release rate at the tip of the interface crack increases, and the interface crack starts to extend. The energy release rate of an interface crack is independent of the crack length when the test piece is under pure bending. For this test method, it is unnecessary to measure the length of the interface crack.